**In The Specification**

At p. 1, before the "Technical Field" section, insert

--**RELATED PATENT DATA**

This patent resulted from a continuation application of U. S. Patent Application Serial No. 09/497,080, filed on February 2, 2000, which resulted from a divisional application of U. S. Patent Application No. 09/113,467, filed on July 10, 1998.--

Please replace the following paragraph on page 2, line 19 to page 3, line 2 with the following paragraph.

A first silicon dioxide layer 24 is formed within openings 22 to a thickness of, for example, about 100 Angstroms. First silicon dioxide layer [[22]] 24 can be formed by, for example, heating substrate 12 in the presence of oxygen. A second silicon dioxide layer 26 is deposited within the openings by high density plasma deposition. In the context of this document, a high density plasma is a plasma having a density of greater than or equal to about $10^{10}$ ions/$cm^3$.

Please replace the following paragraph on page 10, lines 3-7 with the following paragraph.

It is noted that the process of the present invention is described with reference to the reaction chamber construction of Fig. [[9]] 3 for purposes of illustration only. The present invention can, of course, be utilized with other reaction chamber constructions, such as, for example, transformer coupled plasma reactors.